MAX22344/MAX22345/ MAX22346

Reinforced, Fast, Low-Power, Four-Channel 3.75kV_{RMS} Digital Isolators

General Description

The MAX22344–MAX22346 are reinforced, fast, low-power 4-channel digital galvanic isolators using Maxim's proprietary process technology. These devices transfer digital signals between circuits with different power domains, using as little as 0.74mW per channel at 1Mbps (1.8V supply). All of the devices in the family feature reinforced isolation for a withstand voltage rating of 3.75kV_{RMS} for 60 seconds.

The MAX22344–MAX22346 family offers all possible unidirectional channel configurations to accommodate any 4-channel design, including SPI, RS-485, and digital I/O applications. Output enable for the A side of the MAX22345R/S is active-low, making them ideal for isolating a port on a shared SPI bus since the $\overline{\text{CS}}$ signal can directly enable the MISO signal on the isolator. All other output enables in the MAX22344–MAX22346 family are the traditional active-high.

Devices are available with a maximum data rate of either 25Mbps or 200Mbps, and feature a selectable default state for the outputs. The default is the state the output assumes when the input is either not powered or is open-circuit. See the <u>Ordering Information</u> and <u>Product Selector Guide</u> for suffixes associated with each option. Independent 1.71V to 5.5V supplies on each side of the isolator also make the devices suitable for use as level translators.

All of the devices in the MAX22344–MAX22346 family are available in a 20-pin SSOP package with 5.5mm of creepage and clearance. All devices are rated for operation at ambient temperatures of -40°C to +125°C.

Benefits and Features

- Reinforced Galvanic Isolation for Fast Digital Signals
 - Up to 200Mbps Maximum Data Rate
 - Withstands 3.75kV_{RMS} for 60s (V_{ISO})
 - Continuously Withstands 784V_{RMS} (V_{IOWM})
 - Withstands ±10kV Surge between GNDA and GNDB with 1.2/50µs waveform
 - High CMTI (50kV/µs, Typical)
- Low Power Consumption
 - 0.74mW per Channel at 1Mbps with V_{DD} = 1.8V
 - 1.4mW per Channel at 1Mbps with V_{DD} = 3.3V
 - 3.2mW per Channel at 100Mbps with V_{DD} = 1.8V
- Options to Support a Broad Range of Applications
 - 2 Maximum Data Rates (200Mbps, 25Mbps)
 - · 3 Direction Configurations
 - · Active-High or Active-Low Enable Inputs
 - Pin-Selectable Output Default States (High/Low)

Applications

- Isolated SPI Interface
- Fieldbus Communications for Industrial Automation
- Isolated RS-485/RS-422, CAN
- Battery Management
- Medical Systems

Safety Regulatory Approvals (Pending)

- UL According to UL1577
- cUL According to CSA Bulletin 5A
- VDE 0884-11 Reinforced Isolation

<u>Ordering Information</u> and <u>Product Selector Guide</u> appear at end of data sheet.



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Absolute Maximum Ratings

V _{DDA} to GNDA0.3V to +6V	Continuous Power Dissipation (T _A = +70°C)
V _{DDB} to GNDB0.3V to +6V	SSOP (derate 8mW/°C above +70°C)952.4mW
IN_ on Side A, ENA, ENA, DEFA to GNDA0.3V to +6V	Operating Temperature Range40°C to +125°C
IN_ on Side B, ENB, DEFB to GNDB0.3V to +6V	Maximum Junction Temperature+150°C
OUT_ on Side A to GNDA0.3V to (V _{DDA} + 0.3V)	Storage Temperature Range60°C to +150°C
OUT_ on Side B to GNDB0.3V to (V _{DDB} + 0.3V)	Lead Temperature (soldering, 10s)+300°C
Short Circuit Continuous Current	Soldering Temperature (reflow)+260°C
OUT_ on Side A to GNDA,	
OUT on Side B to GNDB±30mA	

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Package Information

PACKAGE TYPE: 20 SSOP						
Package Code	A20MS+7					
Outline Number	21-0056					
Land Pattern Number	90-0094					
THERMAL RESISTANCE, FOUR-LAYER BOARD						
Junction to Ambient (θ _{JA})	84°C/W					
Junction to Case (θ_{JC})	32°C/W					

For the latest package outline information and land patterns (footprints), go to www.maximintegrated.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maximintegrated.com/thermal-tutorial.

DC Electrical Characteristics

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_L=15pF,~T_A=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_A=+25^{\circ}C,~unless~otherwise~noted.)~(Notes~1,~3)$

PARAMETER	SYMBOL	CON	DITIONS	MIN	TYP	MAX	UNITS
POWER SUPPLY	•			'			
Cumply Valtage	V_{DDA}	Relative to GNDA		1.71		5.5	V
Supply Voltage	V_{DDB}	Relative to GNDB		1.71		5.5	7 v
Undervoltage-Lockout Threshold	V _{UVLO} _	V _{DD} _ rising		1.5	1.6	1.66	V
Undervoltage-Lockout Threshold Hysteresis	V _{UVLO_HYST}				45		mV
			V _{DDA} = 5V		0.54	1.00	
		500kHz square	V _{DDA} = 3.3V		0.53	0.97	
Side A Supply Current (MAX22344_) (Note 2)		wave, C _L = 0pF	V _{DDA} = 2.5V		0.52	0.96	
			V _{DDA} = 1.8V		0.50	0.68	
		12.5MHz square wave, C _L = 0pF	V _{DDA} = 5V		1.67	2.50	
			V _{DDA} = 3.3V		1.64	2.43	mA
	I _{DDA}		V _{DDA} = 2.5V		1.62	2.41	
			V _{DDA} = 1.8V		1.58	2.07	
			V _{DDA} = 5V		4.63	6.31	
		50MHz square wave, C _L = 0pF	V _{DDA} = 3.3V		4.53	6.17	
			V _{DDA} = 2.5V		4.48	6.11	
			V _{DDA} = 1.8V		4.34	5.60	
			V _{DDB} = 5V		1.19	2.06	
		500kHz square	V _{DDB} = 3.3V		1.17	2.02	
		wave, C _L = 0pF	V _{DDB} = 2.5V		1.17	2.01	
			V _{DDB} = 1.8V		1.14	1.92	
			V _{DDB} = 5V		2.28	3.29	
Side B Supply Current		12.5MHz square	V _{DDB} = 3.3V		1.85	2.79	7
(MAX22344_) (Note 2)	I _{DDB}	wave, C _L = 0pF	V _{DDB} = 2.5V		1.68	2.58	mA
(11010 =)			V _{DDB} = 1.8V		1.51	2.33	
			V _{DDB} = 5V		5.66	7.07	
		50MHz square wave, C _L = 0pF	V _{DDB} = 3.3V		3.98	5.16	
			V _{DDB} = 2.5V		3.28	4.34	7
			V _{DDB} = 1.8V		2.69	3.59	7

DC Electrical Characteristics (continued)

 $(V_{DDA} - V_{GNDA} = 1.71 \text{V to } 5.5 \text{V}, V_{DDB} - V_{GNDB} = 1.71 \text{V to } 5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = 3.3 \text{V}, V_{DDB} - V_{GNDB} = 3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes } 1, 3)$

PARAMETER	SYMBOL	CON	DITIONS	MIN	TYP	MAX	UNITS
			V _{DDA} = 5V		0.70	1.26	
		500kHz square wave, C _L = 0pF	V _{DDA} = 3.3V		0.69	1.23	
			V _{DDA} = 2.5V		0.68	1.22	
			V _{DDA} = 1.8V		0.66	0.99	
			V _{DDA} = 5V		1.83	2.70	1
Side A Supply Current		12.5MHz square	V _{DDA} = 3.3V		1.70	2.53] .
(MAX22345_) (Note 2)	I _{DDA}	wave, C _L = 0pF	V _{DDA} = 2.5V		1.63	2.45	mA
(V _{DDA} = 1.8V		1.56	2.14	
			V _{DDA} = 5V		4.89	6.51	
		50MHz square	V _{DDA} = 3.3V		4.39	5.93	
		wave, C _L = 0pF	V _{DDA} = 2.5V		4.18	5.67	
			V _{DDA} = 1.8V		3.93	5.11	
			V _{DDB} = 5V		1.03	1.80	
		500kHz square	V _{DDB} = 3.3V		1.01	1.76	
		wave, C _L = 0pF	V _{DDB} = 2.5V		1.01	1.75	mA
			V _{DDB} = 1.8V		0.98	1.61	
			V _{DDB} = 5V		2.13	3.09	
Side B Supply Current		12.5MHz square wave, C _L = 0pF	V _{DDB} = 3.3V		1.80	2.70	
(MAX22345_) (Note 2)	I _{DDB}		V _{DDB} = 2.5V		1.66	2.54	
(V _{DDB} = 1.8V		1.53	2.27	
		50MHz square	V _{DDB} = 5V		5.41	6.88	
			V _{DDB} = 3.3V		4.11	5.41	
		wave, C _L = 0pF	V _{DDB} = 2.5V		3.58	4.78	
			V _{DDB} = 1.8V		3.11	4.11	
			V _{DDA} = 5V		0.87	1.53	
		500kHz square	V _{DDA} = 3.3V		0.85	1.49	
		wave, C _L = 0pF	V _{DDA} = 2.5V		0.84	1.49	1
			V _{DDA} = 1.8V		0.82	1.30	
			V _{DDA} = 5V		1.98	2.89	
Side A Supply Current		12.5MHz square	V _{DDA} = 3.3V		1.75	2.61] .
(MAX22346_) (Note 2)	I _{DDA}	wave, C _L = 0pF	V _{DDA} = 2.5V		1.65	2.49	- mA - - -
(/			V _{DDA} = 1.8V		1.55	2.20	
			V _{DDA} = 5V		5.15	6.69	
		50MHz square	V _{DDA} = 3.3V		4.25	5.66	
		wave, C _L = 0pF	V _{DDA} = 2.5V		3.88	5.22	
			V _{DDA} = 1.8V		3.52	4.60	

DC Electrical Characteristics (continued)

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_L=15pF,~T_A=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_A=+25^{\circ}C,~unless~otherwise~noted.)~(Notes~1,~3)$

PARAMETER	SYMBOL	CON	DITIONS	MIN	TYP	MAX	UNITS
			V _{DDB} = 5V		0.87	1.53	
		500kHz square	V _{DDB} = 3.3V		0.85	1.49	
		wave, C _L = 0pF	V _{DDB} = 2.5V		0.84	1.49	
			V _{DDB} = 1.8V		0.82	1.30	
Side B Supply Current (MAX22346_) (Note 2)			V _{DDB} = 5V		1.98	2.89	
	l===	12.5MHz square	V _{DDB} = 3.3V		1.75	2.61	mA
	I _{DDB}	wave, C _L = 0pF	V _{DDB} = 2.5V		1.65	2.49	
			V _{DDB} = 1.8V		1.55	2.20	
		50MHz square wave, C _L = 0pF	V _{DDB} = 5V		5.15	6.69	
			V _{DDB} = 3.3V		4.25	5.66	
			V _{DDB} = 2.5V		3.88	5.22	
			V _{DDB} = 1.8V		3.52	4.60	
LOGIC INTERFACE (IN_, EN_, EI	NA, DEF_, OUT_)					
		EN_, ENA, IN_	2.25V ≤ V _{DD} _ ≤ 5.5V	0.7 x V _{DD} _			
Input High Voltage	V _{IH}		1.71V ≤ V _{DD} _ < 2.25V	0.75 x V _{DD} _			V
		DEF_ (Note 2)	2.25V ≤ V _{DD} _ ≤ 5.5V	0.7 x V _{DD} _			V
			1.71V ≤ V _{DD} _ < 2.25V	0.75 x V _{DD} _			

DC Electrical Characteristics (continued)

 $(V_{DDA} - V_{GNDA} = 1.71 \text{V to } 5.5 \text{V}, V_{DDB} - V_{GNDB} = 1.71 \text{V to } 5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = 3.3 \text{V}, V_{DDB} - V_{GNDB} = 3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes } 1, 3)$

PARAMETER	SYMBOL	CO	NDITIONS	MIN	TYP	MAX	UNITS
		EN_, ENA, IN_	2.25V ≤ V _{DD} _ ≤ 5.5V			0.8	
Input Low Voltage	V	EN_, ENA, IN_	1.71V ≤ V _{DD} _ < 2.25V			0.7] _v
Input Low Voltage	V _{IL}	DEF (Note 2)	2.25V ≤ V _{DD} _ ≤ 5.5V			8.0]
		DEF_ (Note 2)	1.71V ≤ V _{DD} _ < 2.25V			0.7	
Input Hysteresis	V	EN_, ENA,	MAX2234_B/R		410		mV
input riyatereala	V _{HYS}	DEF_, IN_	MAX2234_C/S		80		IIIV
IN_ Input Pullup Current	I _{PU}	DEFA = DEFB =	high	-10	-5	-1.5	μA
IN_ Input Pulldown Current	I _{PD}	DEFA = DEFB =	low	1.5	5	10	μA
IN_ Input Capacitance	C _{IN}	f _{SW} = 1MHz			2		pF
ENA Pullup Current	I _{PU_ENA}	MAX2234_B/C		-10	-5	-1.5	μA
ENB Pullup Current	I _{PU_ENB}			-10	-5	-1.5	μA
ENA Pulldown Current	I _{PD_EN}	MAX22345R/S		1.5	5	10	μA
DEF_ Pullup Current	l _{PU_DEF}			-10	-5	-1.5	μA
OUT_ Output Voltage High	V _{OH}	I _{OUT} _ = -4mA source		V _{DD} _ - 0.4			V
OUT_ Output Voltage Low	V _{OL}	I _{OUT} = 4mA sin	k			0.4	V

Dynamic Characteristics MAX2234_C/S

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_{L}=15pF,~T_{A}=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_{A}=+25^{\circ}C,~unless~otherwise~noted.)~(Notes~2,~4)$

PARAMETER	SYMBOL	C	CONDITIONS	MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	CMTI	IN_ = GND_ c	IN_ = GND_ or V _{DD_} (Note 5)		50		kV/µs
Mayimum Data Data	DD	2.25V ≤ V _{DD} _	2.25V ≤ V _{DD} ≤ 5.5V				Mhno
Maximum Data Rate	DR _{MAX}	1.71V ≤ V _{DD}	< 2.25V	150			Mbps
Minimum Dulan Width	DW	IN_ to	2.25V ≤ V _{DD} _ ≤ 5.5V			5.00	20
Minimum Pulse Width	PW _{MIN}	OUT_	1.71V ≤ V _{DD} _ < 2.25V			6.67	ns
			4.5V ≤ V _{DD} _ ≤ 5.5V	4.1	5.7	9.2	
		IN_ to	3.0V ≤ V _{DD} ≤ 3.6V	4.2	6.5	10.2	1
	t _{PLH}	OUT_, C _L = 15pF	2.25V ≤ V _{DD} ≤ 2.75V	4.9	7.9	13.4	
Propagation Delay			1.71V ≤ V _{DD} ≤ 1.89V	7.1	12.0	20.3	ns
(Figure 3)		IN_ to OUT_,	4.5V ≤ V _{DD} ≤ 5.5V	4.3	6.1	9.4	1115
	_		3.0V ≤ V _{DD} _ ≤ 3.6V	4.4	6.9	10.5	-
	tPHL	C _I = 15pF	2.25V ≤ V _{DD} _ ≤ 2.75V	5.1	8.2	14.1	
			1.71V ≤ V _{DD} _ ≤ 1.89V	7.2	12.1	21.7	
	PWD	lt _{PLH} - t _{PHL} l	4.5V ≤ V _{DD} _ ≤ 5.5V		0.4	2.0	- ns
Pulse Width Distortion			$3.0V \le V_{DD} \le 3.6V$		0.4	2.0	
Fuise Width Distortion			$2.25V \le V_{DD} \le 2.75V$		0.3	2.0	
			1.71V ≤ V _{DD} _ ≤ 1.89V		0.0	2.0	
		4.5V ≤ V _{DD} _:	≤ 5.5V			3.7	
	t	3.0V ≤ V _{DD} _:	3.0V ≤ V _{DD} ≤ 3.6V			4.3	
	t _{SPLH}	2.25V ≤ V _{DD} _	_ ≤ 2.75V			6.0	
Propagation Delay Skew		1.71V ≤ V _{DD} _	1.71V ≤ V _{DD} ≤ 1.89V			10.3	
Part-to-Part (Same Channel)		4.5V ≤ V _{DD} _:	≤ 5.5V			3.8	ns
	+	3.0V ≤ V _{DD} _:	≤ 3.6V			4.7	
	tsphl	2.25V ≤ V _{DD} ≤ 2.75V				6.5	
		1.71V ≤ V _{DD} _ ≤ 1.89V				11.5	
Propagation Delay Skew Channel-to-Channel		1.71V ≤ V _{DD} _	 1.71V ≤ V _{DD} _ ≤ 5.5V			2.0	ns
(Same Direction)	tscshl	1.71V ≤ V _{DD} _	≤ 5.5V			2.0	115

Dynamic Characteristics MAX2234_C/S (continued)

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_{L}=15pF,~T_{A}=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_{A}=+25^{\circ}C,~unless~otherwise~noted.)~(Notes~2,~4)$

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
		4.5V ≤ V _{DD} _	≤ 5.5V			2.9	
		3.0V ≤ V _{DD} _	$3.0V \le V_{DD} \le 3.6V$			3.4	
	t _{SCOLH}	2.25V ≤ V _{DD}	2.25V ≤ V _{DD} ≤ 2.75V			4.9]
Propagation Delay Skew Channel-to-Channel		1.71V ≤ V _{DD}	_ ≤ 1.89V			10.2	
(Opposite Direction)		4.5V ≤ V _{DD} _	≤ 5.5V			3.2	ns
,	t	3.0V ≤ V _{DD} _	≤ 3.6V			3.8	
	tscohl	2.25V ≤ V _{DD}	_ ≤ 2.75V			5.3	
Dook Eve Diogram litter		1.71V ≤ V _{DD}	_ ≤ 1.89V			10.9	
Peak Eye Diagram Jitter	T _{JIT(PK)}	200Mbps			100		ps
Clock Jitter RMS	T _{JCLK(RMS)}	500kHz clock	input, rising/falling edges		7.5		ps
Rise Time (Figure 3)		C _L = 5pF	4.5V ≤ V _{DD} _ ≤ 5.5V			0.8	- ns
	t _R		$3.0V \le V_{DD} \le 3.6V$			1.1	
	'R		$2.25V \le V_{DD} \le 2.75V$			1.5	
			1.71V ≤ V _{DD} _ ≤ 1.89V			2.4	
			4.5V ≤ V _{DD} _ ≤ 5.5V			1.0	ns
Fall Time	t _F	C. = 5pF	$C_L = 5pF$ $3.0V \le V_{DD} \le 3.6V$			1.4	
(Figure 3)	4	CL = SPF	$2.25V \le V_{DD} \le 2.75V$			1.9	
			1.71V ≤ V _{DD} _ ≤ 1.89V			3.0	
		ENA to	4.5V ≤ V _{DD} _ ≤ 5.5V			3.9	
Enable to Data Valid		OUT_,	$3.0V \le V_{DD} \le 3.6V$			6.4	
(Figure 4)	tEN	EN_ to OUT_,	2.25V ≤ V _{DD} _ ≤ 2.75V			10.1	ns
		C _L = 15pF	1.71V ≤ V _{DD} _ ≤ 1.89V			18.4	
		ENA to	4.5V ≤ V _{DD} _ ≤ 5.5V			6.3	ns
Enable to Tristate	tro	OUT_, EN_ to OUT_,	$3.0V \le V_{DD} \le 3.6V$			9.0	
(Figure 4)	t _{TRI}		$2.25V \le V_{DD} \le 2.75V$			12.6	
		C _L = 15pF	1.71V ≤ V _{DD} _ ≤ 1.89V			19.2	

Dynamic Characteristics MAX2234_B/R

 $(V_{DDA}-V_{GNDA}=1.71V~to~5.5V,~V_{DDB}-V_{GNDB}=1.71V~to~5.5V,~C_{L}=15pF,~T_{A}=-40^{\circ}C~to~+125^{\circ}C,~unless~otherwise~noted.~Typical~values~are~at~V_{DDA}-V_{GNDA}=3.3V,~V_{DDB}-V_{GNDB}=3.3V,~V_{GNDA}=V_{GNDB},~T_{A}=+25^{\circ}C,~unless~otherwise~noted.)~(Notes~2,~4)$

PARAMETER	SYMBOL		CONDITIONS	MIN	TYP	MAX	UNITS
Common-Mode Transient Immunity	СМТІ	IN_ = GND_ o	IN_ = GND_ or VDD_ (Note 5)		50		kV/µs
Maximum Data Rate	DR _{MAX}			25			Mbps
Minimum Pulse Width	PW _{MIN}	IN_ to OUT_				40	ns
Glitch Rejection		IN_ to OUT_		10	17	29	ns
			4.5V ≤ V _{DD} _ ≤ 5.5V	17.4	24.2	32.5	
		IN_ to	$3.0V \le V_{DD} \le 3.6V$	17.6	25.0	33.7	
	t _{PLH}	OUT_, C _L = 15pF	2.25V ≤ V _{DD} _ ≤ 2.75V	18.3	26.4	36.7	
Propagation Delay		SE .SP.	1.71V ≤ V _{DD} ≤ 1.89V	20.7	30.6	43.5	
(Figure 3)			4.5V ≤ V _{DD} ≤ 5.5V	16.9	24.0	33.6	ns
		IN_to	3.0V ≤ V _{DD} ≤ 3.6V	17.2	24.8	35.1	
	t _{PHL}	OUT_, C _L = 15pF	2.25V ≤ V _{DD} _ ≤ 2.75V	17.8	26.1	38.2]
		SE .SP.	1.71V ≤ V _{DD} _ ≤ 1.89V	19.8	30.0	45.8	
			4.5V ≤ V _{DD} _ ≤ 5.5V		0.2	4.0	
Dulas Width Distortion	DWD	1, ,	$3.0V \le V_{DD} \le 3.6V$		0.2	4.0	ns
Pulse Width Distortion	PWD	tplh - tphl	2.25V ≤ V _{DD} ≤ 2.75V		0.3	4.0	
			1.71V ≤ V _{DD} _ ≤ 1.89V		0.6	4.0	
		4.5V ≤ V _{DD} _	≤ 5.5V			15.1	
	t _{SPLH}	3.0V ≤ V _{DD} _:	≤ 3.6V			15.0	
		2.25V ≤ V _{DD} _	2.25V ≤ V _{DD} _ ≤ 2.75V			15.4	
Propagation Delay Skew		1.71V ≤ V _{DD} _	$1.71V \le V_{DD_{\perp}} \le 1.89V$			20.5	ne
Part-to-Part (Same Channel)		4.5V ≤ V _{DD} _:	4.5V ≤ V _{DD} _ ≤ 5.5V			13.9	ns
	t	$3.0V \le V_{DD} \le 3.6V$				14.2	
	tsphl	2.25V ≤ V _{DD} _ ≤ 2.75V				16.0	
		1.71V ≤ V _{DD} ≤ 1.89V				21.8	
Propagation Delay Skew Channel-to-Channel	tscslh	1.71V ≤ V _{DD} _	_ ≤ 5.5V			2.0	ns
(Same Direction)	tscshl	1.71V ≤ V _{DD} _	_ ≤ 5.5V			2.0	115
		4.5V ≤ V _{DD} _	≤ 5.5V			13.9	
	tagayy	3.0V ≤ V _{DD} _:	≤ 3.6V			13.7]
	t _{SCOLH}					14.2	
Propagation Delay Skew		 1.71V ≤ V _{DD} _ ≤ 1.89V				19.4	no
Channel-to-Channel (Opposite Direction)		4.5V ≤ V _{DD} _	≤ 5.5V			13.0	ns
(5663010 511001011)		3.0V ≤ V _{DD} _	3.0V ≤ V _{DD} ≤ 3.6V			12.9	
	teconi —	2.25V ≤ V _{DD}	2.25V ≤ V _{DD} ≤ 2.75V			14.4	
		1.71V ≤ V _{DD} _	≤ 1.89V			20.1	

Dynamic Characteristics MAX2234_B/R (continued)

 $(V_{DDA} - V_{GNDA} = 1.71 \text{V to } 5.5 \text{V}, V_{DDB} - V_{GNDB} = 1.71 \text{V to } 5.5 \text{V}, C_L = 15 \text{pF}, T_A = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}, \text{ unless otherwise noted. Typical values are at } V_{DDA} - V_{GNDA} = 3.3 \text{V}, V_{DDB} - V_{GNDB} = 3.3 \text{V}, V_{GNDA} = V_{GNDB}, T_A = +25 ^{\circ}\text{C}, \text{ unless otherwise noted.)} \text{ (Notes 2, 4)}$

PARAMETER	SYMBOL	(CONDITIONS	MIN	TYP	MAX	UNITS
Peak Eye Diagram Jitter	T _{JIT(PK)}	25Mbps			250		ps
			4.5V ≤ V _{DD} _ ≤ 5.5V			0.8	
Rise Time		C - 575	3.0V ≤ V _{DD} _ ≤ 3.6V			1.1	
(Figure 3)	t _R	C _L = 5pF	2.25V ≤ V _{DD} _ ≤ 2.75V			1.5	ns
			1.71V ≤ V _{DD} _ ≤ 1.89V			2.4	
Fall Time (Figure 3)			4.5V ≤ V _{DD} _ ≤ 5.5V			1.0	
	+ _	C _L = 5pF	3.0V ≤ V _{DD} _≤ 3.6V			1.4	ns
	t _F		2.25V ≤ V _{DD} _ ≤ 2.75V			1.9	
			1.71V ≤ V _{DD} _ ≤ 1.89V			3.0	
		ENA to OUT_, EN_ to OUT_,	4.5V ≤ V _{DD} _ ≤ 5.5V			3.9	ns
Enable to Data Valid			3.0V ≤ V _{DD} _ ≤ 3.6V			6.4	
(Figure 4)	t _{EN}		2.25V ≤ V _{DD} _ ≤ 2.75V			10.1	
		C _L = 15pF	1.71V ≤ V _{DD} _ ≤ 1.89V			18.4	
Enable to Tristate (Figure 4)		ENA to	4.5V ≤ V _{DD} _ ≤ 5.5V			6.3	ns
	+	OUT_, EN_ to OUT_,	$3.0V \le V_{DD} \le 3.6V$			9.0	
	t _{TRI}		$2.25V \le V_{DD} \le 2.75V$			12.6	
		C _L = 15pF	1.71V ≤ V _{DD} _ ≤ 1.89V			19.2	

- **Note 1:** All devices are 100% production tested at T_A = +125°C. Specifications over temperature are guaranteed by design and characterization.
- Note 2: Not production tested. Guaranteed by design and characterization.
- **Note 3:** All currents into the device are positive. All currents out of the device are negative. All voltages are referenced to their respective ground (GNDA or GNDB), unless otherwise noted.
- **Note 4:** All measurements taken with $V_{DDA} = V_{DDB}$, unless otherwise noted.
- Note 5: CMTI is the maximum sustainable common-mode voltage slew rate while maintaining the correct output. CMTI applies to both rising and falling common-mode voltage edges. Tested with the transient generator connected between GNDA and GNDB (V_{CM} = 1000V).

ESD Protection

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
ESD		Human Body Model, All Pins		±4		kV

Table 1. Insulation Characteristics

PARAMETER	SYMBOL	CONDITIONS	VALUE	UNITS	
Partial Discharge Test Voltage	V _{PR}	Method B1 = V _{IORM} x 1.875 (t = 1s, partial discharge < 5pC)	2078	V _P	
Maximum Repetitive Peak Isolation Voltage	V _{IORM}	(Note 6)	1108	V _P	
Maximum Working Isolation Voltage	V _{IOWM}	Continuous RMS voltage (Note 6)	784	V_{RMS}	
Maximum Transient Isolation Voltage	V _{IOTM}	t = 1s	5300	V _P	
Maximum Withstand Isolation Voltage	V _{ISO}	f _{SW} = 60Hz, duration = 60s (Note 7)	3750	V_{RMS}	
Maximum Surge Isolation Voltage	V _{IOSM}	Basic Insulation, 1.2/50µs pulse per IEC61000-4-5	10	kV	
		V _{IO} = 500V, T _A = 25°C	>10 ¹²		
Insulation Resistance	R _{IO}	V _{IO} = 500V, 100°C ≤ T _A ≤ 125°C	>10 ¹¹	Ω	
		V _{IO} = 500V at T _S = 150°C	>109		
Barrier Capacitance Side A to Side B	CIO	f _{SW} = 1MHz (Note 8)	1.5	pF	
Minimum Creepage Distance	CPG		5.5	mm	
Minimum Clearance Distance	CLR		5.5	mm	
Internal Clearance		Distance through insulation	0.021	mm	
Comparative Tracking Index	СТІ	Material Group II (IEC 60112)	>400		
Climate Category			40/125/21		
Pollution Degree (DIN VDE 0110, Table 1)			2		

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Safety Limits

Damage to the IC can result in a low-resistance path to ground or to the supply and, without current limiting, the MAX22344–MAX22346 could dissipate excessive amounts of power. Excessive power dissipation can damage the die and result in damage to the isolation barrier, potentially causing downstream issues. Table 2 shows the safety limits for the MAX22344–MAX22346.

The maximum safety temperature (T_S) for the device is the 150°C maximum junction temperature specified in the Absolute Maximum Ratings. The power dissipation (P_D) and junction-to-ambient thermal impedance (θ_{JA}) deter-

mine the junction temperature. Thermal impedance values (θ_{JA} and θ_{JC}) are available in the Package Thermal Characteristics section of the datasheet and power dissipation calculations are discussed in the Calculating Power Dissipation section. Calculate the junction temperature (T_{J}) as:

$$T_J = T_A + (P_D \times \theta_{JA})$$

<u>Figure 1</u> and <u>Figure 2</u> show the thermal derating curve for safety limiting the power and the current of the device. Ensure that the junction temperature does not exceed 150°C.

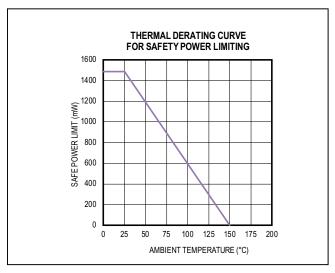


Figure 1. Thermal Derating Curve for Safety Power Limiting

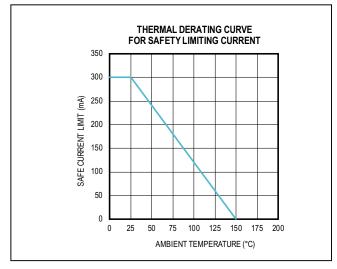


Figure 2. Thermal Derating Curve for Safety Current Limiting

Table 2. Safety Limiting Values for the MAX22344-MAX22346

PARAMETER	SYMBOL	TEST CONDITIONS	MAX	UNIT
Safety Current on Any Pin	IS	T _J = 150°C, T _A = 25°C	300	mA
Total Safety Power Dissipation	P_{S}	T _J = 150°C, T _A = 25°C	1448	mW
Maximum Safety Temperature	T _S		150	°C

Test Circuits and Timing Diagrams

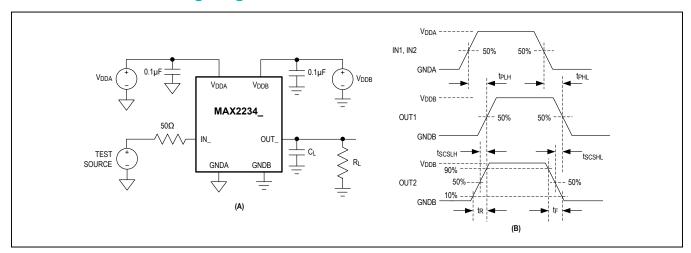


Figure 3. Test Circuit (A) and Timing Diagram (B)

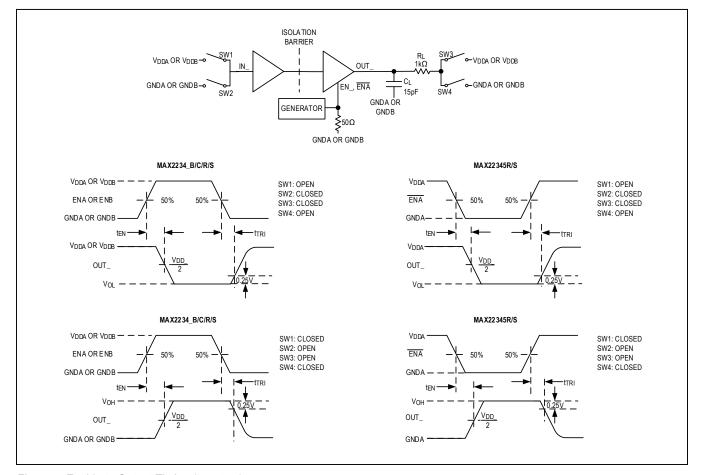
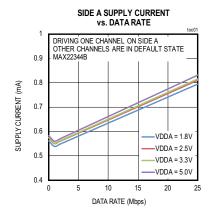
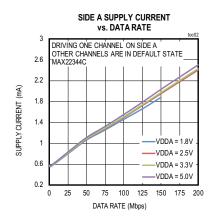


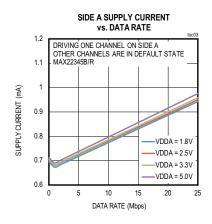
Figure 4. Enable to Output Timing (t_{EN}, t_{TRI})

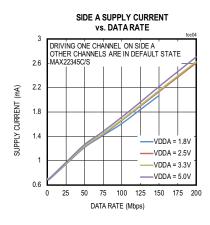
Typical Operating Characteristics

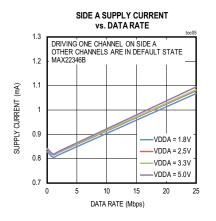
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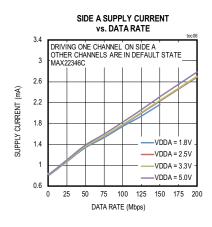


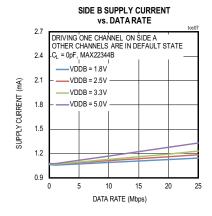


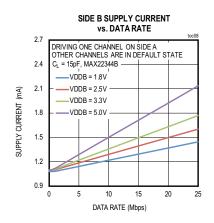






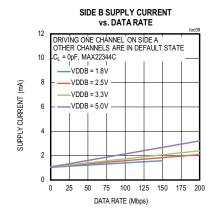


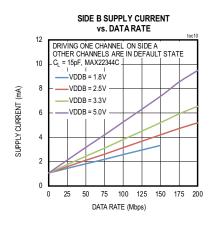


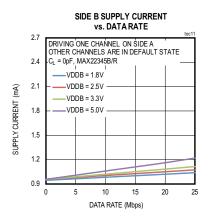


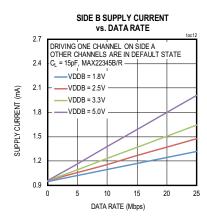
Typical Operating Characteristics (continued)

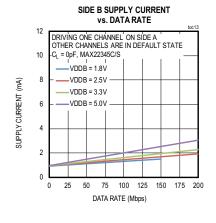
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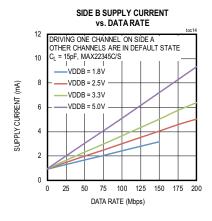


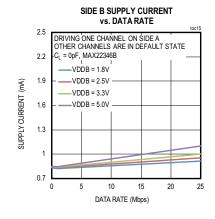


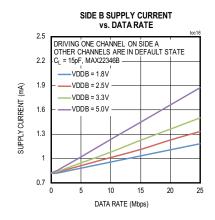






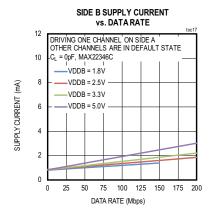


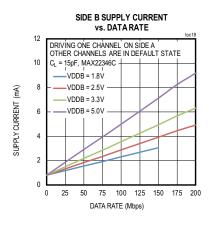


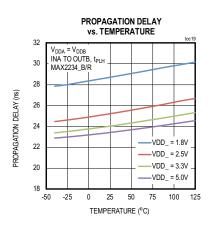


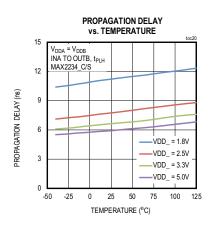
Typical Operating Characteristics (continued)

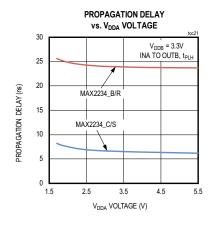
 $(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25$ °C, unless otherwise noted.)

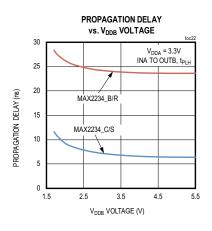


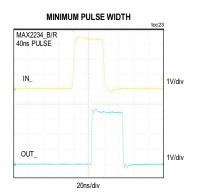


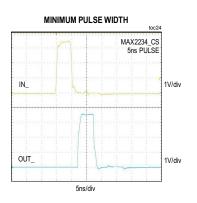






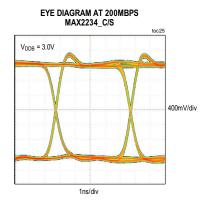


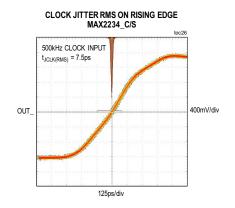


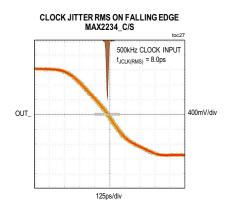


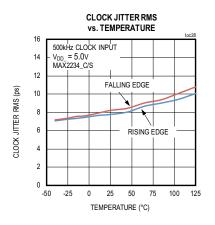
Typical Operating Characteristics (continued)

(V_{DDA} - V_{GNDA} = +3.3V, V_{DDB} - V_{GNDB} = +3.3V, V_{GNDA} = V_{GNDB}, T_A = +25°C, unless otherwise noted.)

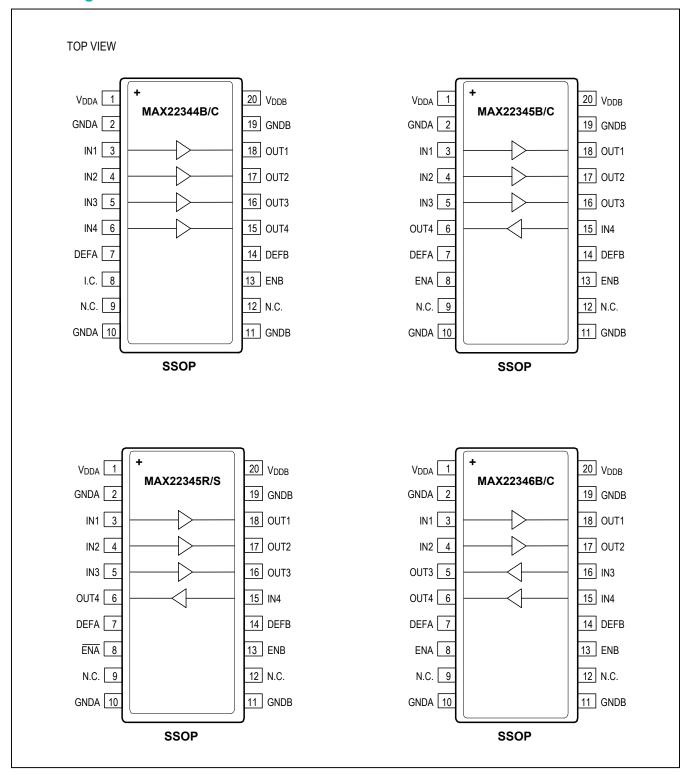








Pin Configurations



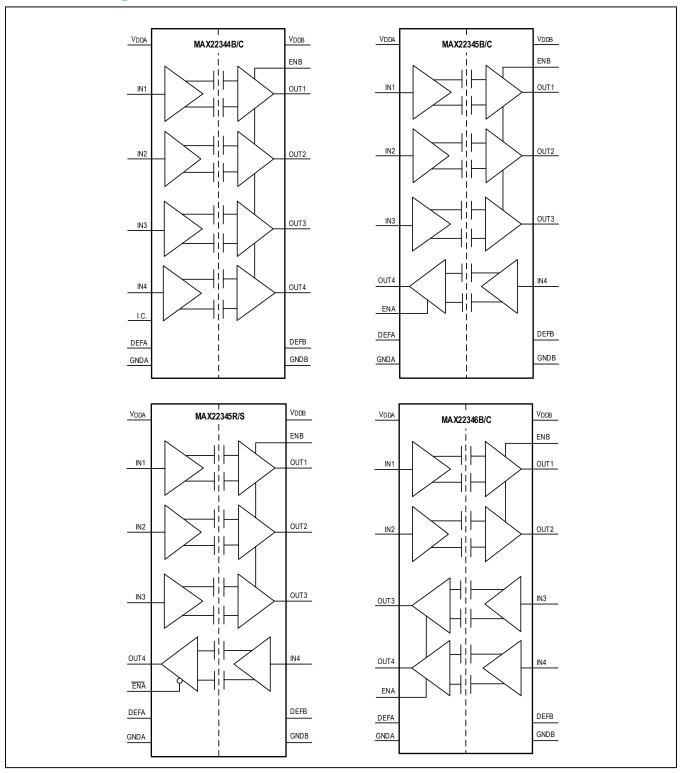
Pin Description

	PIN							
NAME	MAX22344B/C	MAX22345B/C	MAX22345R/S	MAX22346B/C				
V _{DDA}	1	1	1	1				
GNDA	2, 10	2, 10	2, 10	2, 10				
IN1	3	3	3	3				
IN2	4	4	4	4				
IN3	5	5	5	16				
IN4	6	15	15	15				
DEFA	7	7	7	7				
I.C.	8	_	_	_				
N.C.	9, 12	9, 12	9, 12	9, 12				
ENA	_	8	_	8				
ENA	_	_	8	_				
GNDB	11, 19	11, 19	11, 19	11, 19				
ENB	13	13	13	13				
DEFB	14	14	14	14				
OUT4	15	6	6	6				
OUT3	16	16	16	5				
OUT2	17	17	17	17				
OUT1	18	18	18	18				
V _{DDB}	20	20	20	20				

Pin Description (continued)

NAME	FUNCTION
POWER	
V_{DDA}	Power Supply Input for Side A. Bypass V _{DDA} to GNDA with a 0.1µF ceramic capacitor as close as possible to the pin.
GNDA	Ground Reference for Side A.
V_{DDB}	Power Supply Input for Side B. Bypass V _{DDB} to GNDB with a 0.1µF ceramic capacitor as close as possible to the pin.
GNDB	Ground reference for Side B.
INPUTS	
IN1	Logic Input 1 on Side A. Corresponds to Logic Output 1 on Side B.
IN2	Logic Input 2 on Side A. Corresponds to Logic Output 2 on Side B.
IN3	Logic Input 3 on Side A/B. Corresponds to Logic Output 3 on Side B/A.
IN4	Logic Input 4 on Side A/B. Corresponds to Logic Output 4 on Side B/A.
OUTPUTS	
OUT1	Logic Output 1 on Side B. OUT1 is the logic output for the IN1 input on Side A.
OUT2	Logic Output 2 on Side B. OUT2 is the logic output for the IN2 input on Side A.
OUT3	Logic Output 3 on Side B/A. OUT3 is the logic output for the IN3 input on Side A/B.
OUT4	Logic Output 4 on Side B/A. OUT4 is the logic output for the IN4 input on Side A/B.
ENABLE INPUTS	
ENA	Active-High Enable for Side A. ENA has an internal 5μA pull-up to V _{DDA} .
ENA	Active-Low Enable for Side A. ENA has an internal 5μA pull-down to GNDA.
ENB	Active-High Enable for Side B. ENB has an internal 5µA pull-up to V _{DDB} .
DEFAULT CONTROL	- -
DEFA	Default Control Input for Side A. Connect DEFA to V _{DDA} to set side A outputs to a default-high state and to enable the pullup current on side A inputs. Connect DEFA to GNDA to set side A outputs to a default-low state and enable the pulldown current on side A inputs. DEFA must be tied to the same state (high or low) as DEFB.
DEFB	Default Control Input for Side B. Connect DEFB to V _{DDB} to set side B outputs to a default-high state and to enable the pullup current on side B inputs. Connect DEFB to GNDB to set side B outputs to a default-low state and enable the pulldown current on side B inputs. DEFB must be tied to the same state (high or low) as DEFA.
INTERNALLY CONN	ECTED, NOT CONNECTED
I.C.	Internally Connected. Leave unconnected or connect to GNDA or V _{DDA} .
N.C.	Not Connected. Not internally connected.

Functional Diagram



Detailed Description

The MAX22344–MAX22346 are a family of 4-channel reinforced digital isolators. The MAX22344–MAX22346 have an isolation rating of 3.75kV_{RMS}. The MAX22344–MAX22346 family offers all possible unidirectional channel configurations to accommodate any 4-channel design, including SPI, RS-232, RS-485, and digital I/O applications. For applications requiring bidirectional channels, such as I²C, see the MAX14933 and MAX14937.

The MAX22344 features four channels transferring digital signals in one direction for applications such as isolated digital I/O. The MAX22345 has three channels transmitting data in one direction and one channel transmitting in the opposite direction, making them ideal for applications such as isolated SPI and RS-485 communication. The MAX22346 provides further design flexibility with two channels in each direction for isolated RS-232 or other applications.

Devices are available in a 20-pin SSOP package and are rated for up to 3.75kV_{RMS}. This family of digital isolators offers low-power operation, high electromagnetic interference (EMI) immunity, and stable temperature performance through Maxim's proprietary process technology. The devices isolate different ground domains and block high-voltage/high-current transients from sensitive or human interface circuitry.

Devices are available with a maximum data rate of either 25Mbps (B/R versions) or 200Mbps (C/S versions). All devices feature user-selectable default-high or default-low outputs. The default is the state the output assumes when the input is not powered or if the input is open-circuit. The devices have two supply inputs (V_{DDA} and V_{DDB}) that independently set the logic levels on either side of the device. V_{DDA} and V_{DDB} are referenced to GNDA and GNDB, respectively. The MAX22344–MAX22346 also feature a refresh circuit to ensure output accuracy when an input remains in the same state indefinitely.

Digital Isolation

The MAX22344–MAX22346 provide reinforced galvanic isolation for digital signals that are transmitted between two ground domains. The devices withstand differences of up to $3.75 \text{kV}_{\text{RMS}}$ for up to 60 seconds, and up to $1108 \text{V}_{\text{PFAK}}$ of continuous isolation.

Level-Shifting

The wide supply voltage range of both V_{DDA} and V_{DDB} allows the MAX22344–MAX22346 to be used for level translation in addition to isolation. V_{DDA} and V_{DDB} can be independently set to any voltage from 1.71V to 5.5V. The supply voltage sets the logic level on the corresponding side of the isolator.

Unidirectional Channels

Each channel of the MAX22344–MAX22346 is unidirectional; it only passes data in one direction, as indicated in the functional diagram. Each device features four unidirectional channels that operate independently with guaranteed data rates from DC up to 25Mbps (B/R versions), or from DC to 200Mbps (C/S versions). The output driver of each channel is push-pull, eliminating the need for pullup resistors. The outputs are able to drive both TTL and CMOS logic inputs.

Startup and Undervoltage-Lockout

The V_{DDA} and V_{DDB} supplies are both internally monitored for undervoltage conditions. Undervoltage events can occur during power-up, power-down, or during normal operation due to a sagging supply voltage. When an undervoltage condition is detected on either supply while the outputs are enabled, all outputs go to their default states regardless of the state of the inputs (Table 3 , Table 4). Figure 5 through Figure 8 show the behavior of the outputs during power-up and power-down.

Table 3. MAX2234_B/C Output Behavior During Undervoltage Conditions

V _{IN} _	V _{DDA}	V _{DDB}	ENA	ENB	V _{OUTA}	V _{OUTB}	
4		Powered	1	1	High	High	
'	Powered		0	0	Hi-Z	Hi-Z	
0	0 Powered	Davis and Davis	Dawarad	1	1	Low	Low
0		Powered	0	0	Hi-Z	Hi-Z	
V	X Undervoltage	ndervoltage Powered	1	1	Default	Default	
X			0	0	Hi-Z	Hi-Z	
X	Y	red Undervoltage	1	1	Default	Default	
^	Powered		0	0	Hi-Z	Hi-Z	

Table 4. MAX22345R/S Output Behavior During Undervoltage Conditions

V _{IN} _	V _{DDA}	V _{DDB}	ENA	ENB	V _{OUTA}	V _{OUTB}	
1			0	1	High	High	
'	Powered	Powered	1	0	Hi-Z	Hi-Z	
0	0 Powered	Damard	Dawarad	0	1	Low	Low
0		Powered	1	0	Hi-Z	Hi-Z	
V	X Undervoltage	Jndervoltage Powered	0	1	Default	Default	
X			1	0	Hi-Z	Hi-Z	
V	X Powered	d. Hadaaalkaa	0	1	Default	Default	
^		Powered Undervoltage 1	1	0	Hi-Z	Hi-Z	

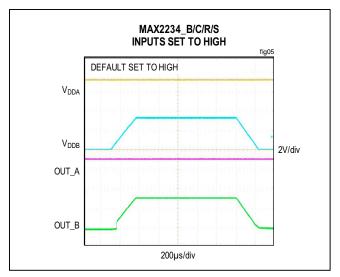


Figure 5. Undervoltage Lockout Behavior (MAX2234_ High)

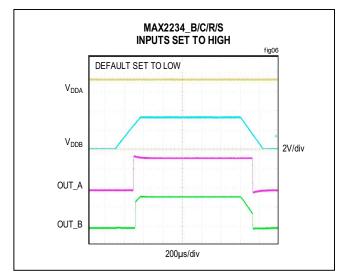


Figure 6. Undervoltage Lockout Behavior (MAX2234_ High)

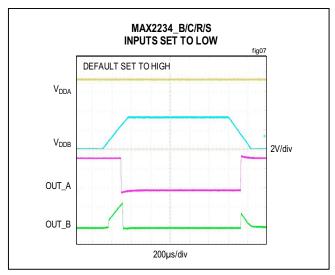


Figure 7. Undervoltage Lockout Behavior (MAX2234_ Low)

Selectable Output Default (DEFA, DEFB)

The default is the state the output assumes when the input is not powered or if the input is open circuit. The MAX22344-MAX22346 feature user-selectable default-high or default-low outputs. Set both DEFA and DEFB high to set all channels to default-high, or set both DEFA and DEFB low to set all channels to default-low.

Ensure the logic state (high or low) of DEFA is the same as that for DEFB. Do not toggle DEFA or DEFB during normal operation.

Applications Information

Power-Supply Sequencing

The MAX22344-MAX22346 do not require special power supply sequencing. The logic levels are set independently on either side by V_{DDA} and V_{DDB} . Each supply can be present over the entire specified range regardless of the level or presence of the other supply.

Power-Supply Decoupling

To reduce ripple and the chance of introducing data errors, bypass V_{DDA} and V_{DDB} with 0.1µF low-ESR ceramic capacitors to GNDA and GNDB, respectively. Place the bypass capacitors as close to the power supply input pins as possible.

Layout Considerations

The PCB designer should follow some critical recommendations in order to get the best performance from the design.

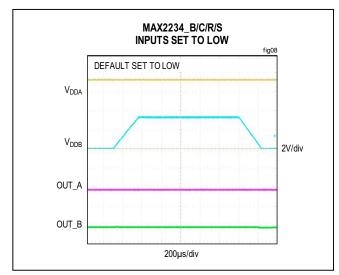


Figure 8. Undervoltage Lockout Behavior (MAX2234 Low)

- Keep the input/output traces as short as possible. To keep signal paths low-inductance, avoid using vias.
- Have a solid ground plane underneath the highspeed signal layer.
- Keep the area underneath the MAX22344–MAX22346 free from ground and signal planes. Any galvanic or metallic connection between the Side A and Side B defeats the isolation.

Calculating Power Dissipation

The required current for a given supply (V_{DDA} or V_{DDB}) can be estimated by summing the current required for each channel. The supply current for a channel depends on whether the channel is an input or an output, the channel's data rate, and the capacitive or resistive load if it is an output. The typical current for an input or output at any data rate can be estimated from the graphs in Figure 9 and Figure 10. Please note the data in Figure 9 and Figure 10 are extrapolated from the supply current measurements in a typical operating condition.

The total current for a single channel is the sum of the "no load" current (shown in Figure 9 and Figure 10) which is a function of Voltage and Data Rate, and the "load current," which depends on the type of load. Current into a capacitive load is a function of the load capacitance, the switching frequency, and the supply voltage.

$$I_{CL} = C_L \times f_{SW} \times V_{DD}$$

where

 I_{CL} is the current required to drive the capacitive load. C_L is the load capacitance on the isolator's output pin.

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f_{SW} is the switching frequency (bits per second/2).

V_{DD} is the supply voltage on the output side of the isolator. Current into a resistive load depends on the load resistance, the supply voltage and the average duty cycle of the data waveform. The DC load current can be conservatively estimated by assuming the output is always high.

$$I_{RL} = V_{DD} \div R_{L}$$

where

 I_{RL} is the current required to drive the resistive load. V_{DD} is the supply voltage on the output side of the isolator. R_{L} is the load resistance on the isolator's output pin.

Example (shown in Figure 11): A MAX22345C is operating with V_{DDA} = 2.5V, V_{DDB} = 3.3V, channel 1 operating at 20Mbps with a 10pF capacitive load, channel 2 held high with a 10kΩ resistive load, and channel 4 operating at 100Mbps with a 15pF capacitive load. Channel 3 is not in use and the resistive load is negligible since the isolator is driving a CMOS input. Refer to Table 5 and Table 6 for V_{DDA} and V_{DDB} supply current calculation worksheets.

VDDA must supply:

 Channel 1 is an input channel operating at 2.5V and 20Mbps, consuming 0.33mA, estimated from Figure 9.

- Channel 2 and 3 are input channels operating at 2.5V with DC signal, consuming 0.14mA, estimated from Figure 9.
- Channel 4 is an output channel operating at 2.5V and 100Mbps, consuming 0.77mA, estimated from Figure 10.
- I_{CL} on channel 4 for 15pF capacitor at 2.5V and 100Mbps is 1.875mA.

Total current for side A = $0.33 + 0.14 \times 2 + 0.77 + 1.875 = 3.255$ mA, typical

V_{DDB} must supply:

- Channel 1 is an output channel operating at 3.3V and 20Mbps, consuming 0.40mA, estimated from Figure 10.
- Channel 2 and 3 are output channels operating at 3.3V with DC signal, consuming 0.27mA, estimated from Figure 10.
- Channel 4 is an input channel operating at 3.3V and 100Mbps, consuming 1.11mA, estimated from Figure 9.
- I_{CL} on channel 1 for 10pF capacitor at 3.3V and 20Mbps is 0.33mA.
- I_{RL} on channel 2 for 10kΩ resistor held at 3.3V is 0.33mA.

Total current for side B = $0.40 + 0.27 \times 2 + 1.11 + 0.33 + 0.33 = 2.71$ mA, typical

Table 5. Side A Supply Current Calculation Worksheet

SIDE A	V _{DDA} = 2.5V							
Channel	IN/ OUT	Data Rate (Mbps)	Load Type	Load	"No Load" Current (mA)	Load Current (mA)		
1	IN	20			0.33			
2	IN	0			0.14			
3	IN	0			0.14			
4	OUT	100	Capacitive	15pF	0.77	2.5V x 50MHz x 15pF = 1.875mA		
	Total: 3.26mA							

Table 6. Side B Supply Current Calculation Worksheet

SIDE B	V _{DDB} = 3.3V							
Channel	IN/ OUT	Data Rate (Mbps)	Load Type	Load	"No Load" Current (mA)	Load Current (mA)		
1	OUT	20	Capacitive	10pF	0.40	3.3V x 10MHz x 10pF = 0.33mA		
2	OUT	0	Resistive	10kΩ	0.27	3.3V / 10kΩ = 0.33mA		
3	OUT	0			0.27			
4	IN	100			1.11			
	Total: 2.71mA							

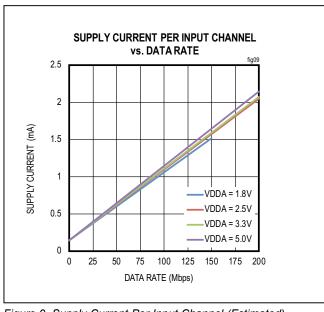


Figure 9. Supply Current Per Input Channel (Estimated)

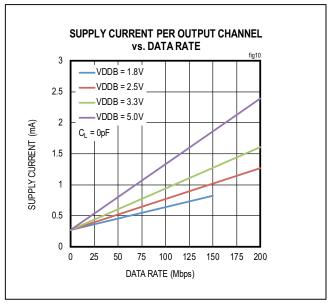


Figure 10. Supply Current Per Output Channel (Estimated)

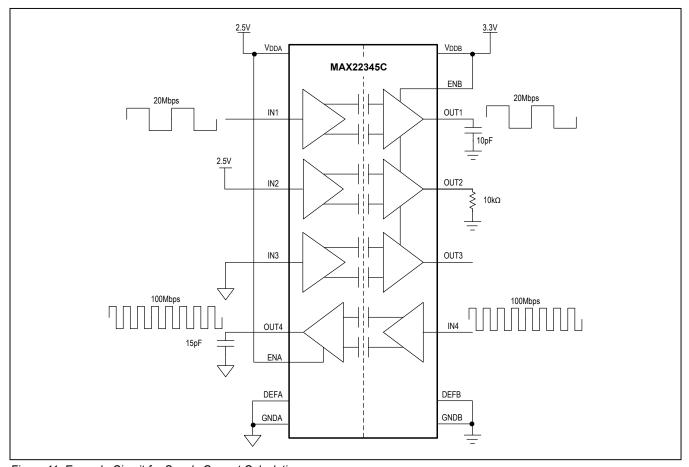
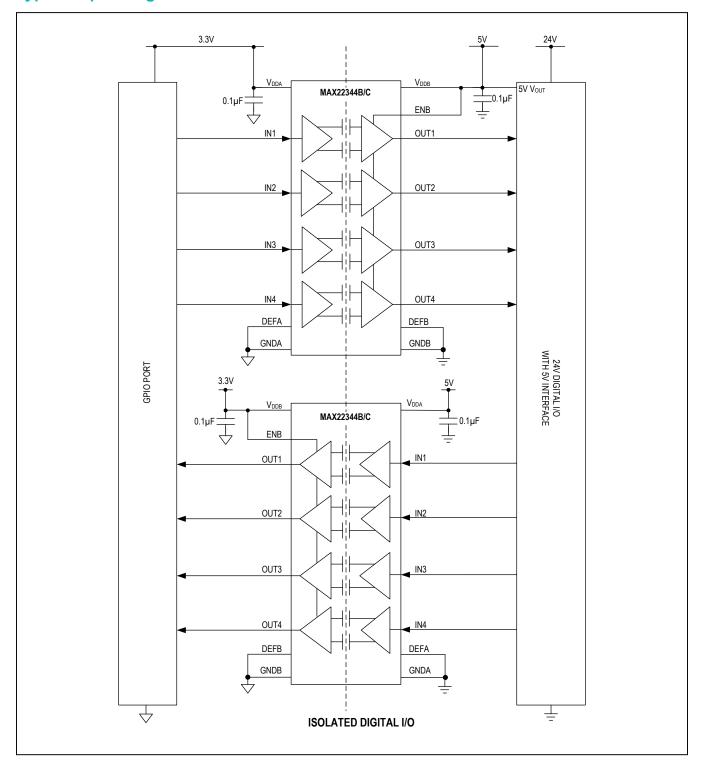
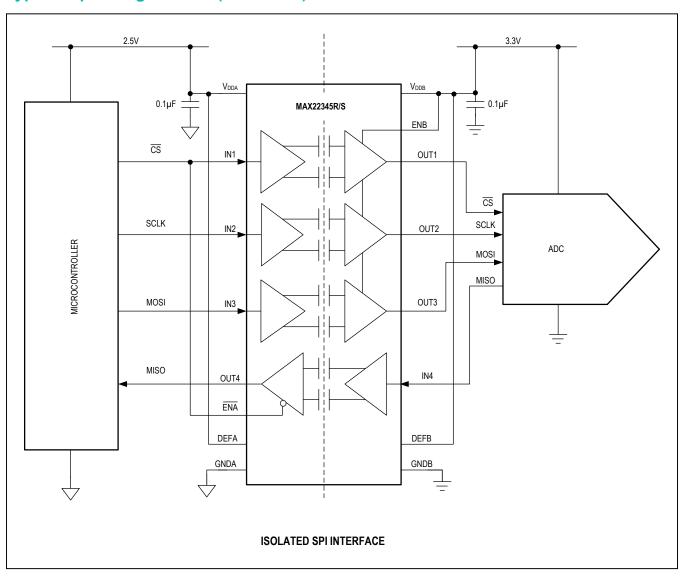


Figure 11. Example Circuit for Supply Current Calculation

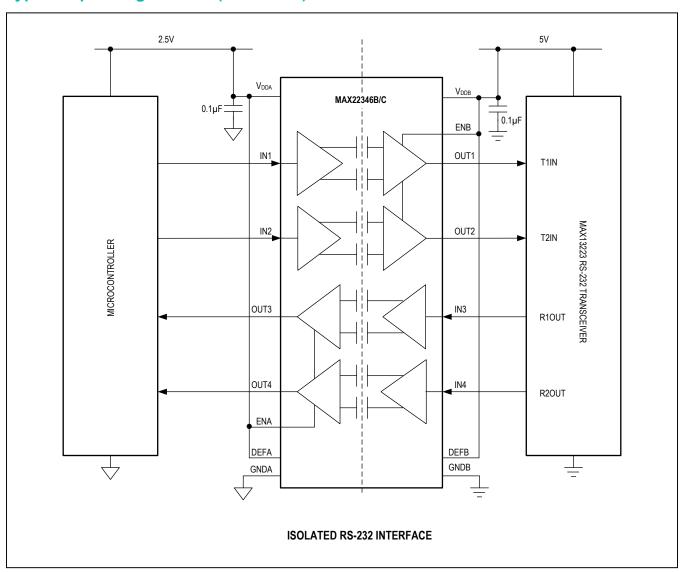
Typical Operating Circuits



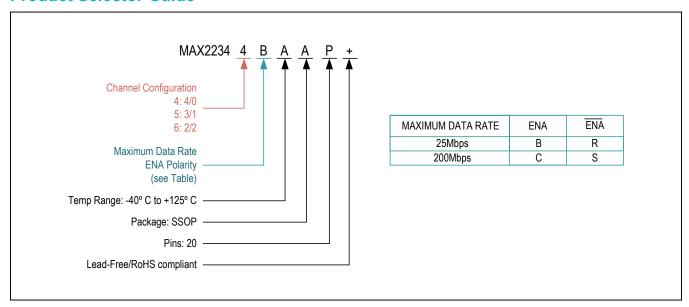
Typical Operating Circuits (continued)



Typical Operating Circuits (continued)



Product Selector Guide



Ordering Information

PART	CHANNEL CONFIGU- RATION	DATA RATE (Mbps)	ENA POLARITY	ISOLATION VOLTAGE (kV _{RMS})	TEMP RANGE (°C)	PIN- PACKAGE
MAX22344 BAAP+*	4/0	25	_	3.75	-40 to +125	20 SSOP
MAX22344CAAP+	4/0	200	_	3.75	-40 to +125	20 SSOP
MAX22345BAAP+*	3/1	25	Active-High	3.75	-40 to +125	20 SSOP
MAX22345CAAP+*	3/1	200	Active-High	3.75	-40 to +125	20 SSOP
MAX22345RAAP+*	3/1	25	Active-Low	3.75	-40 to +125	20 SSOP
MAX22345SAAP+	3/1	200	Active-Low	3.75	-40 to +125	20 SSOP
MAX22346BAAP+*	2/2	25	Active-High	3.75	-40 to +125	20 SSOP
MAX22346CAAP+	2/2	200	Active-High	3.75	-40 to +125	20 SSOP

^{*}Future product—contact factory for availability.

Chip Information

PROCESS: BICMOS

⁺Denotes a lead(Pb)-free/RoHS-compliant package.

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Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	2/18	Initial release	_
1	10/18	Updated title, added future product designation to MAX22344CAAP+ and removed it from MAX22345SAAP+ in the <i>Ordering Information</i> table.	1–30
2	2/19	Removed future product designation from MAX22344CAAP+ in the <i>Ordering Information</i> table.	30
3	3/19	Removed future product designation from MAX22346CAAP+ in the <i>Ordering Information</i> table.	30

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